



MMBT4403T

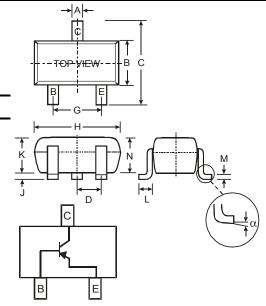
PNP SMALL SIGNAL SURFACE MOUNT TRANSISTOR

Features

- **Epitaxial Planar Die Construction**
- Complementary NPN Type Available (MMBT4401T)
- Ultra-Small Surface Mount Package
- Lead Free/RoHS Compliant (Note 2)
- "Green" Device (Note 3 and 4)

Mechanical Data

- Case: SOT-523
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Solderable per MIL-STD-202, Method 208
- Lead Free Plating (Matte Tin Finish annealed over Alloy 42 leadframe).
- Terminal Connections: See Diagram
- Marking Information: 2T, See Page 4
- Ordering & Date Code Information: See Page 4
- Weight: 0.002 grams (approximate)



SOT-523								
Dim	Min	Max	Тур					
Α	0.15	0.30	0.22					
В	0.75	0.85	0.80					
C	1.45	1.75	1.60					
D	_	_	0.50					
G	0.90	1.10	1.00					
н	1.50	1.70	1.60					
J	0.00	0.10	0.05					
K	0.60	0.80	0.75					
L	0.10	0.30	0.22					
М	0.10	0.20	0.12					
N	0.45	0.65	0.50					
α	0°	8°	_					
All Dimensions in mm								

Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic		Symbol	Value	Unit	
Collector-Base Voltage		V _{CBO}	-40	V	
Collector-Emitter Voltage		V _{CEO}	-40	V	
Emitter-Base Voltage		V_{EBO}	-5.0	V	
Collector Current – Continuous	(Note 1)	Ic	-600	mA	
Power Dissipation	(Note 1)	Pd	150	mW	
Thermal Resistance, Junction to Ambient	(Note 1)	$R_{ heta JA}$	833	°C/W	
Operating and Storage Temperature Range		T _j , T _{STG}	-55 to +150	°C	

Notes:

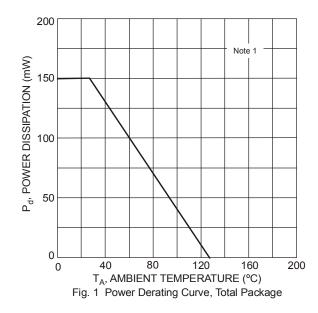
- 1. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.
- No purposefully added lead
- Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
 Product manufactured with Date Code UO (week 40, 2007) and newer are built with Green Molding Compound. Product manufactured prior to Date Code UO are built with Non-Green Molding Compound and may contain Halogens or Sb2O3 Fire Retardants.

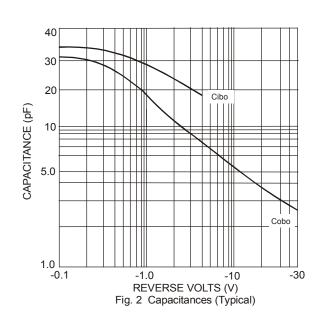


Electrical Characteristics @TA = 25°C unless otherwise specified

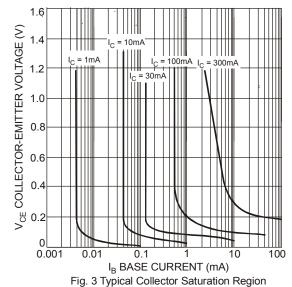
Characteristic		Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 5)					
Collector-Base Breakdown Voltage	V _{(BR)CBO}	-40	_	V	$I_C = -100 \mu A, I_E = 0$
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	-40	_	V	$I_C = -1.0 \text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	-5.0	_	V	$I_E = -100 \mu A, I_C = 0$
Collector Cutoff Current	I _{CEX}	_	-100	nA	$V_{CE} = -35V, V_{EB(OFF)} = -0.4V$
Base Cutoff Current	I _{BL}	_	-100	nA	$V_{CE} = -35V, V_{EB(OFF)} = -0.4V$
ON CHARACTERISTICS (Note 5)					
DC Current Gain	h _{FE}	30 60 100 100 20		_	$\begin{split} I_{C} &= -100 \mu \text{A}, \ V_{CE} = -1.0 \text{V} \\ I_{C} &= -1.0 \text{mA}, \ V_{CE} = -1.0 \text{V} \\ I_{C} &= -150 \text{mA}, \ V_{CE} = -1.0 \text{V} \\ I_{C} &= -150 \text{mA}, \ V_{CE} = -2.0 \text{V} \\ I_{C} &= -500 \text{mA}, \ V_{CE} = -2.0 \text{V} \end{split}$
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	_	-0.40 -0.75	V	I_C = -150mA, I_B = -15mA I_C = -500mA, I_B = -50mA
Base-Emitter Saturation Voltage		-0.75 —	-0.95 -1.30	V	I_C = -150mA, I_B = -15mA I_C = -500mA, I_B = -50mA
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	$C_{\sf cb}$	_	8.5	pF	$V_{CB} = -10V$, $f = 1.0MHz$, $I_E = 0$
Input Capacitance	C_{eb}	_	30	pF	$V_{EB} = -0.5V$, $f = 1.0MHz$, $I_C = 0$
Input Impedance	h _{ie}	1.5	15	kΩ	
Voltage Feedback Ratio	h _{re}	0.1	8.0	x 10 ⁻⁴	$V_{CE} = -10V, I_{C} = -1.0mA,$
Small Signal Current Gain	h _{fe}	60	500	_	f = 1.0kHz
Output Admittance	h _{oe}	1.0	100	μS	
Current Gain-Bandwidth Product	f⊤	200	_	MHz	$V_{CE} = -10V, I_{C} = -20mA,$ f = 100MHz
SWITCHING CHARACTERISTICS		•			
Delay Time	t _d		15	ns	$V_{CC} = -30V$, $I_{C} = -150mA$,
Rise Time	t _r	_	20	ns	$V_{BE(off)} = -2.0V, I_{B1} = -15mA$
Storage Time	ts	_	225	ns	$V_{CC} = -30V, I_{C} = -150mA,$
Fall Time	t _f		30	ns	$I_{B1} = I_{B2} = -15\text{mA}$

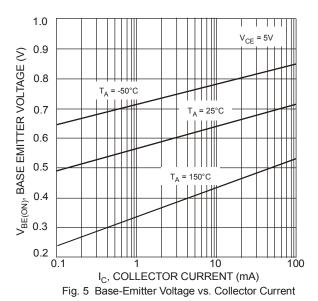
Notes: 5. Short duration pulse test used to minimize self-heating effect.

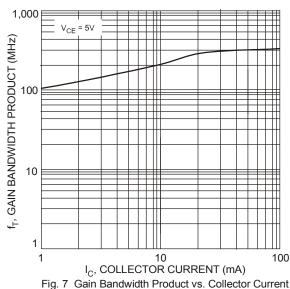












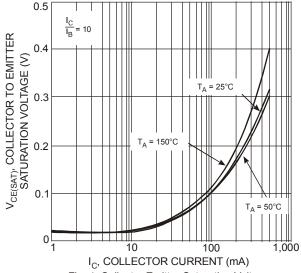


Fig. 4 Collector Emitter Saturation Voltage vs. Collector Current

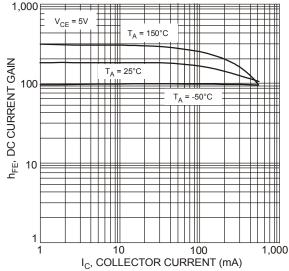


Fig. 6 DC Current Gain vs. Collector Current

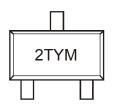


Ordering Information (Note 6)

Device	Packaging	Shipping			
MMBT4403T-7-F	SOT-523	3000/Tape & Reel			

Notes: 6. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information



2T = Product Type Marking Code YM = Date Code Marking Y = Year (ex: N = 2002) M = Month (ex: 9 = September)

Date Code Key

Date odd Noj												
Year	2002	2003	2004	2005	200)6 20	007	2008	2009	2010	2011	2012
Code	N	Р	R	S	Т		U	V	W	Х	Υ	Z
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	l Aug	g Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

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